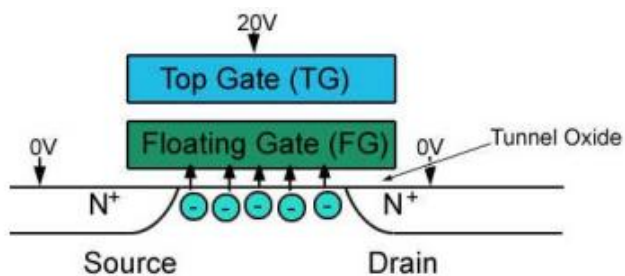
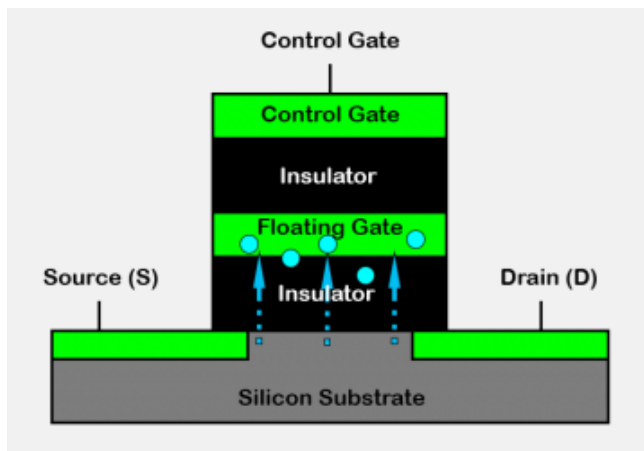
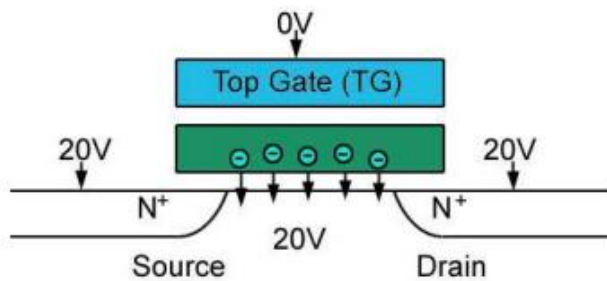
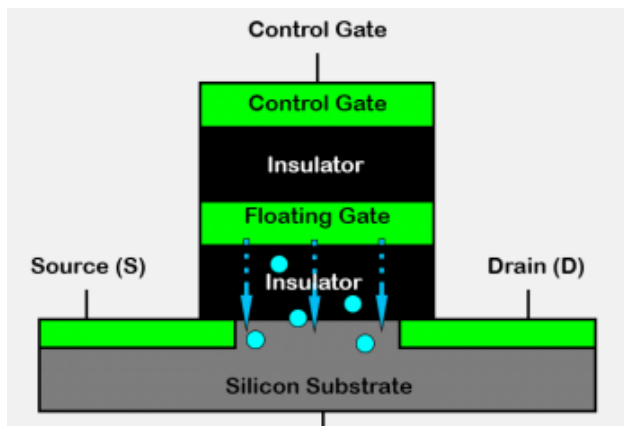


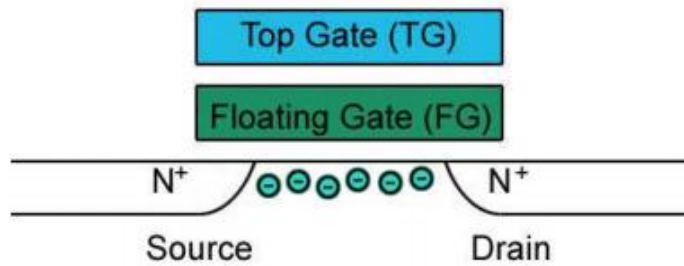
FLOATING GATE STATE	REFERRED TO AS	BINARY VALUE ASSIGNED
CHARGED	PROGRAMMED	ZERO - 0
NO CHARGE	ERASED	ONE - 1



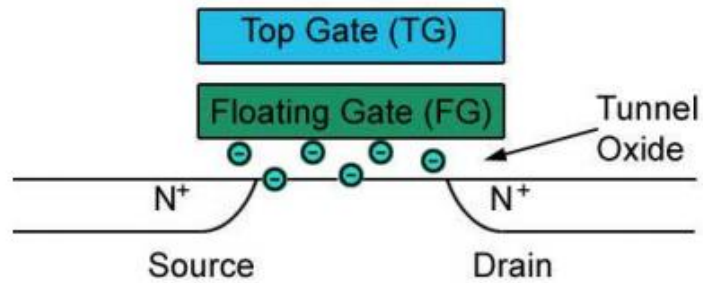
Programming



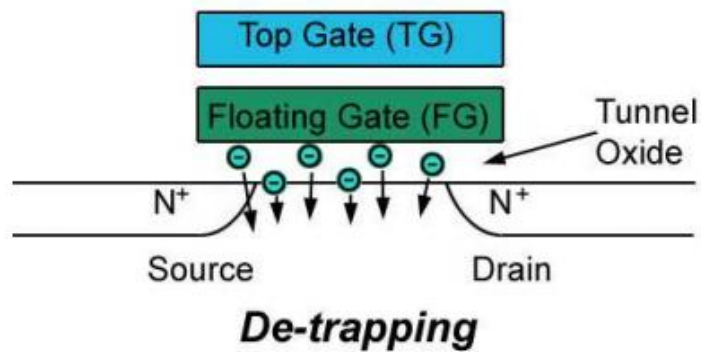
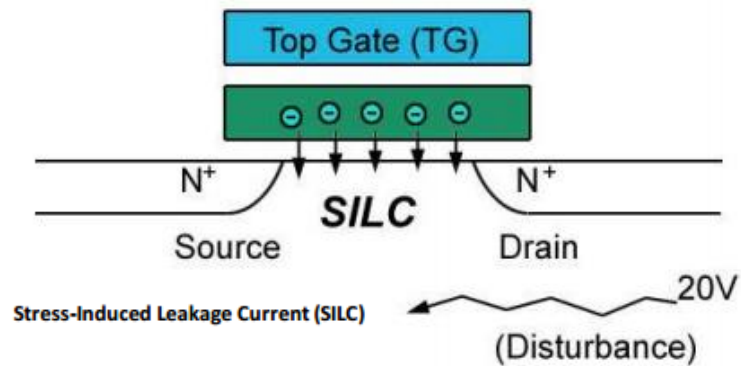
Erase



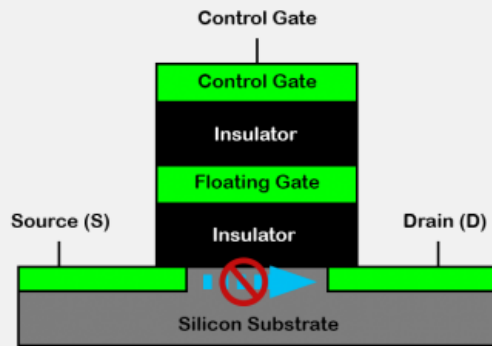
New NAND Flash Memory Cell



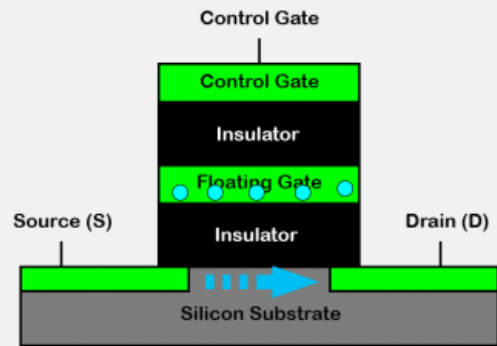
End Of Life NAND Flash Memory Cell



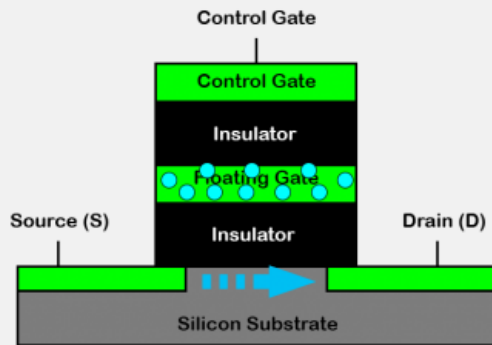
SLC, MLC and TLC NAND Flash



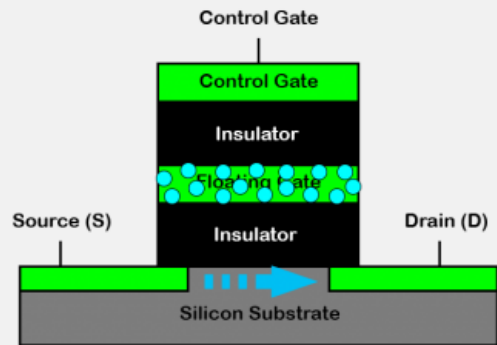
State 1 - No Charge



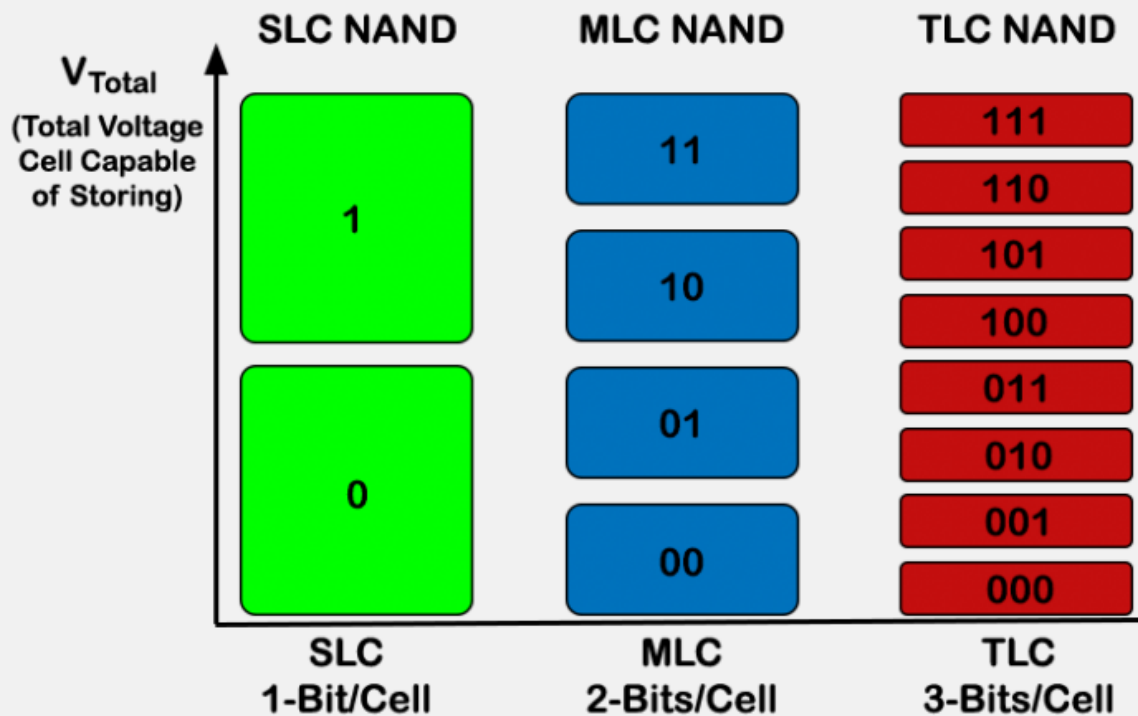
State 2 - Lightly Charged



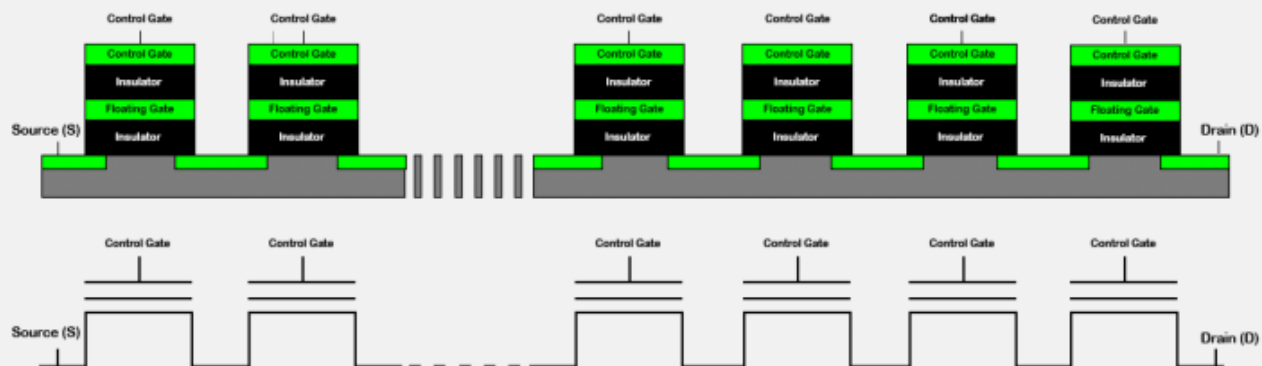
State 3 - Medium Charge



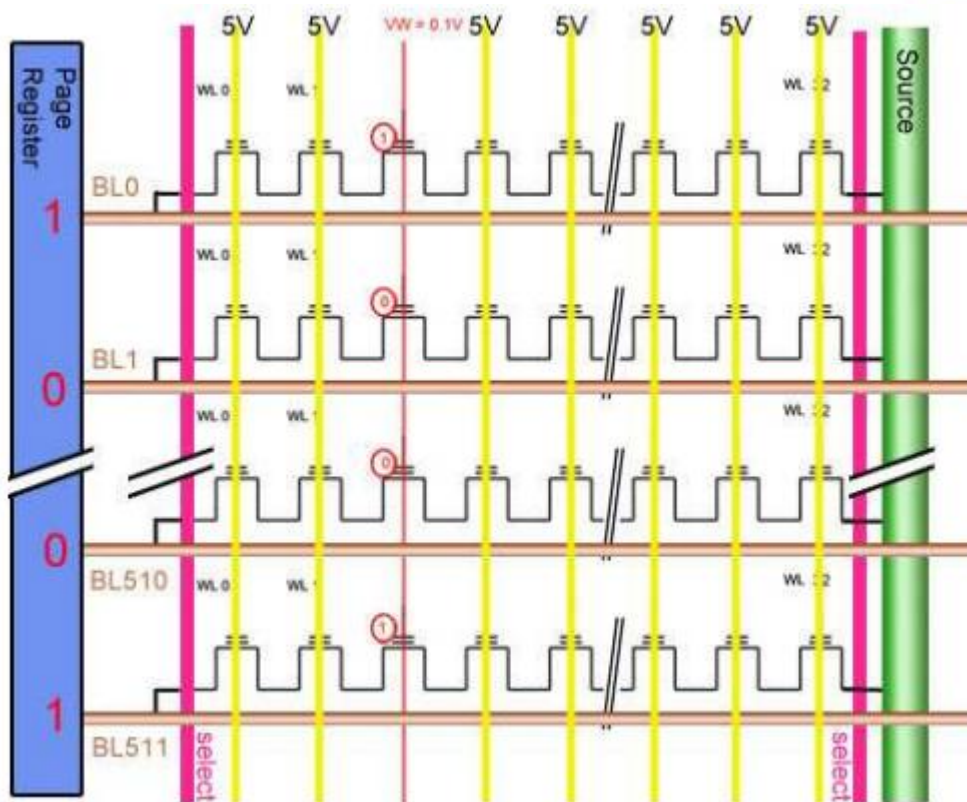
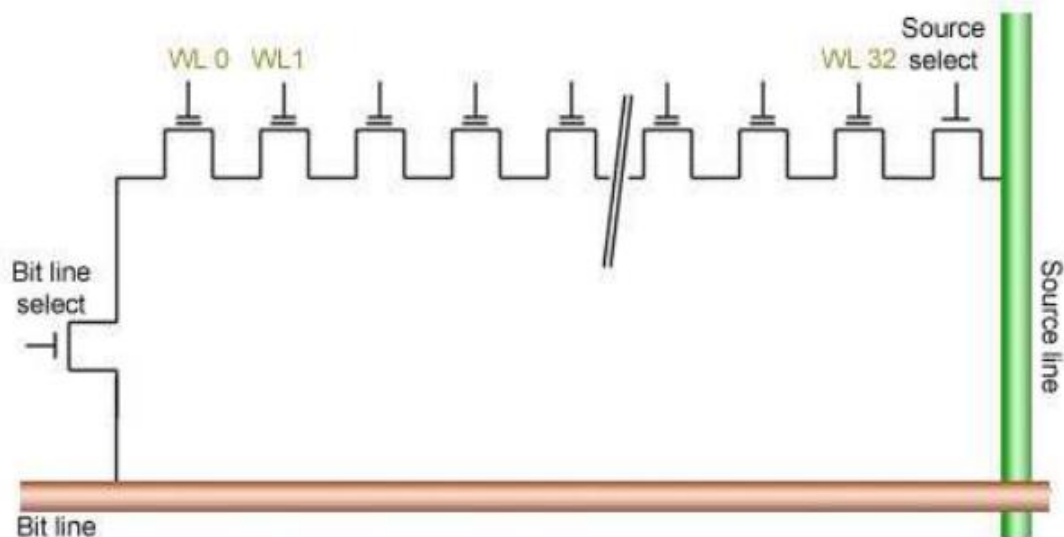
State 4 - Highly Charged

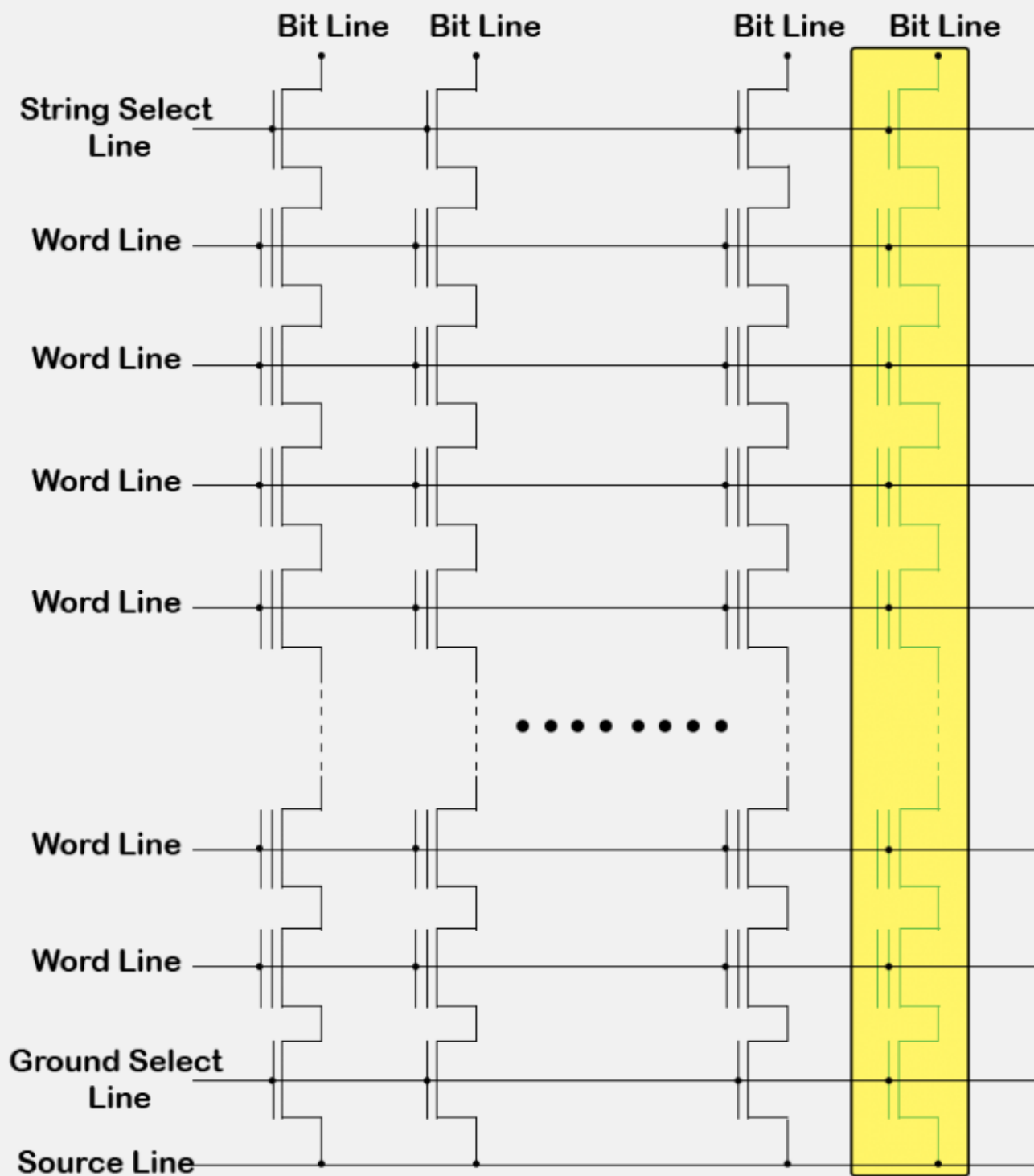


Voltage Allocated to each State based on NAND Flash Technology

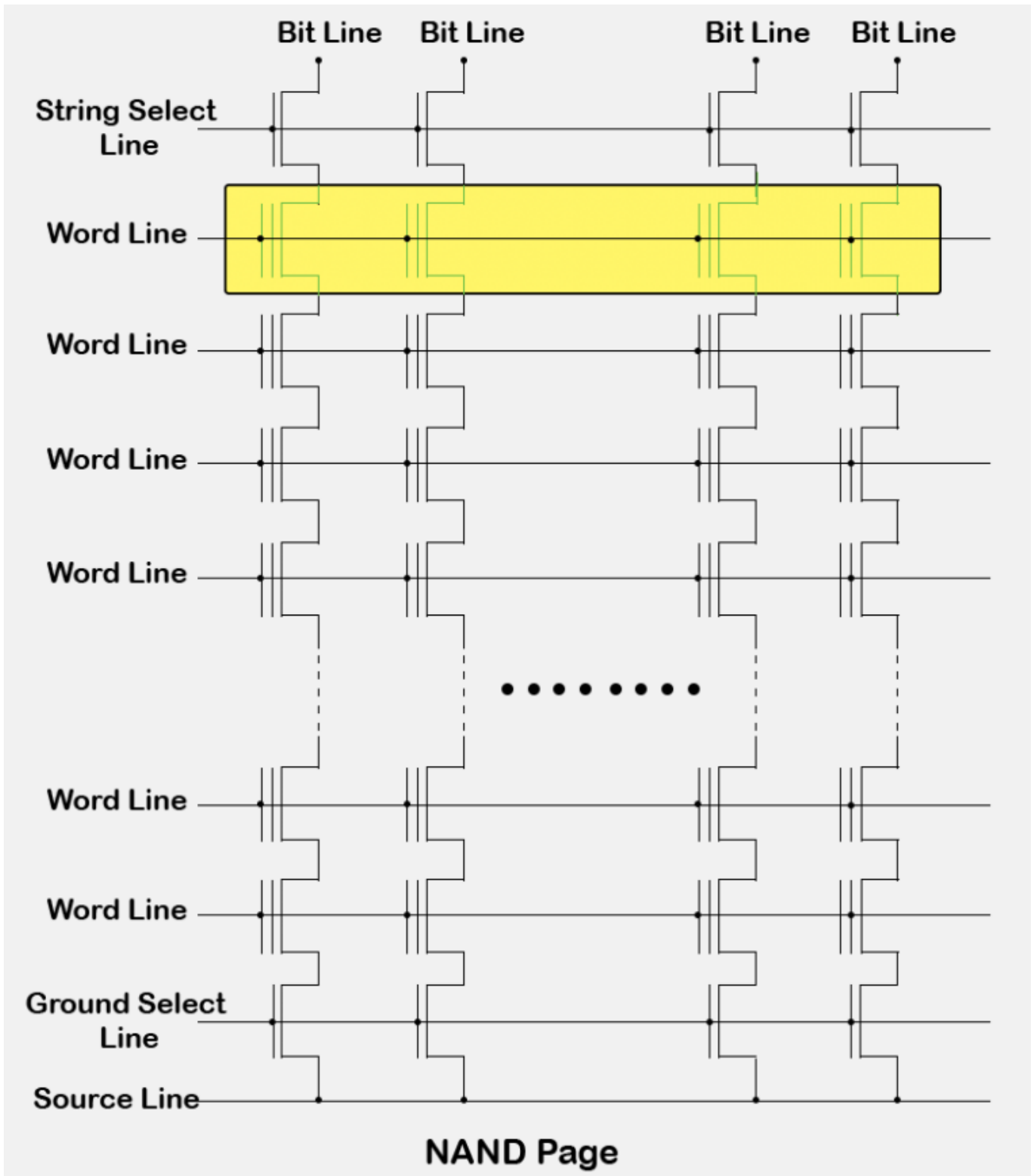


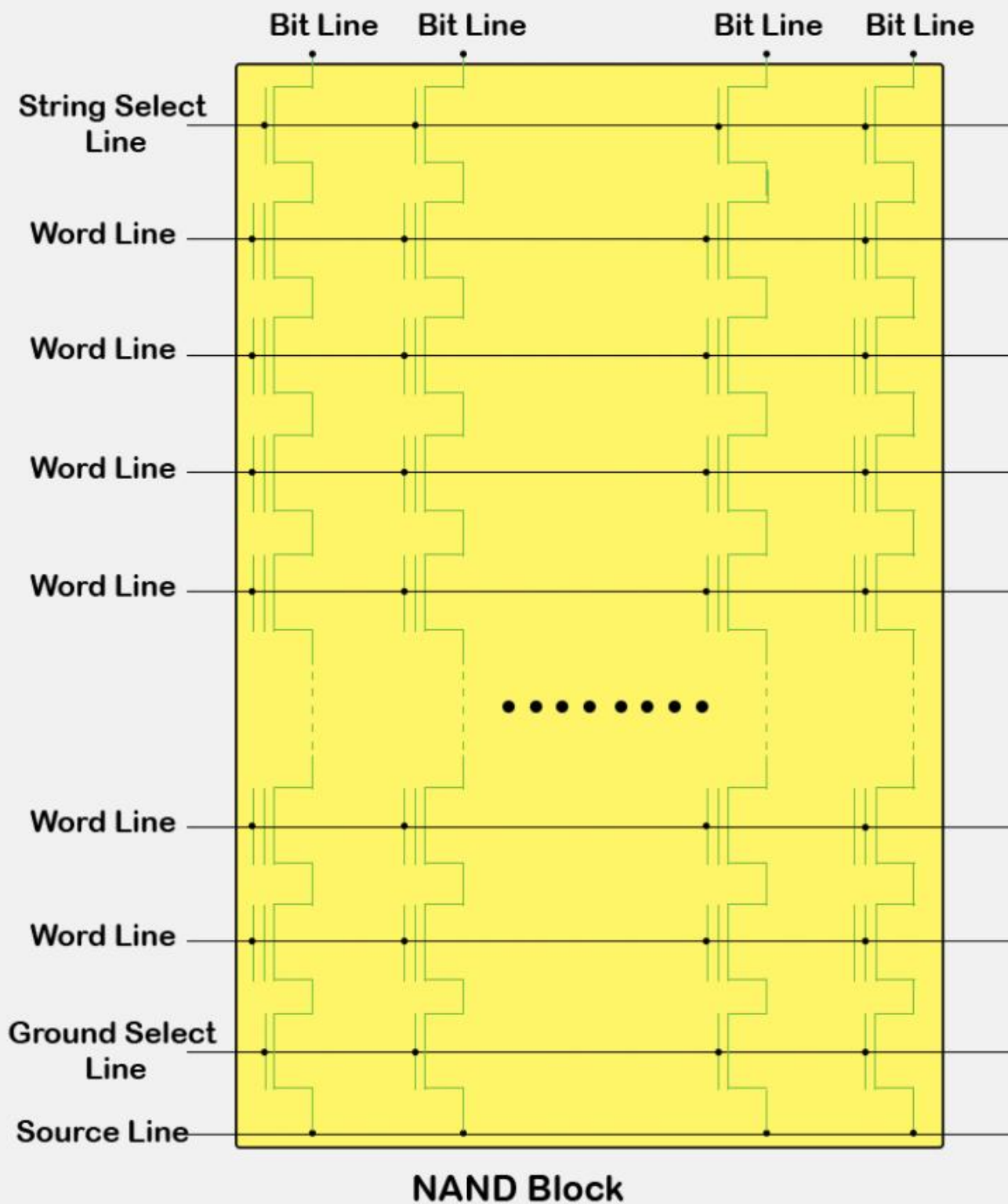
NAND String (Shown in Diagram and Schematic Versions)

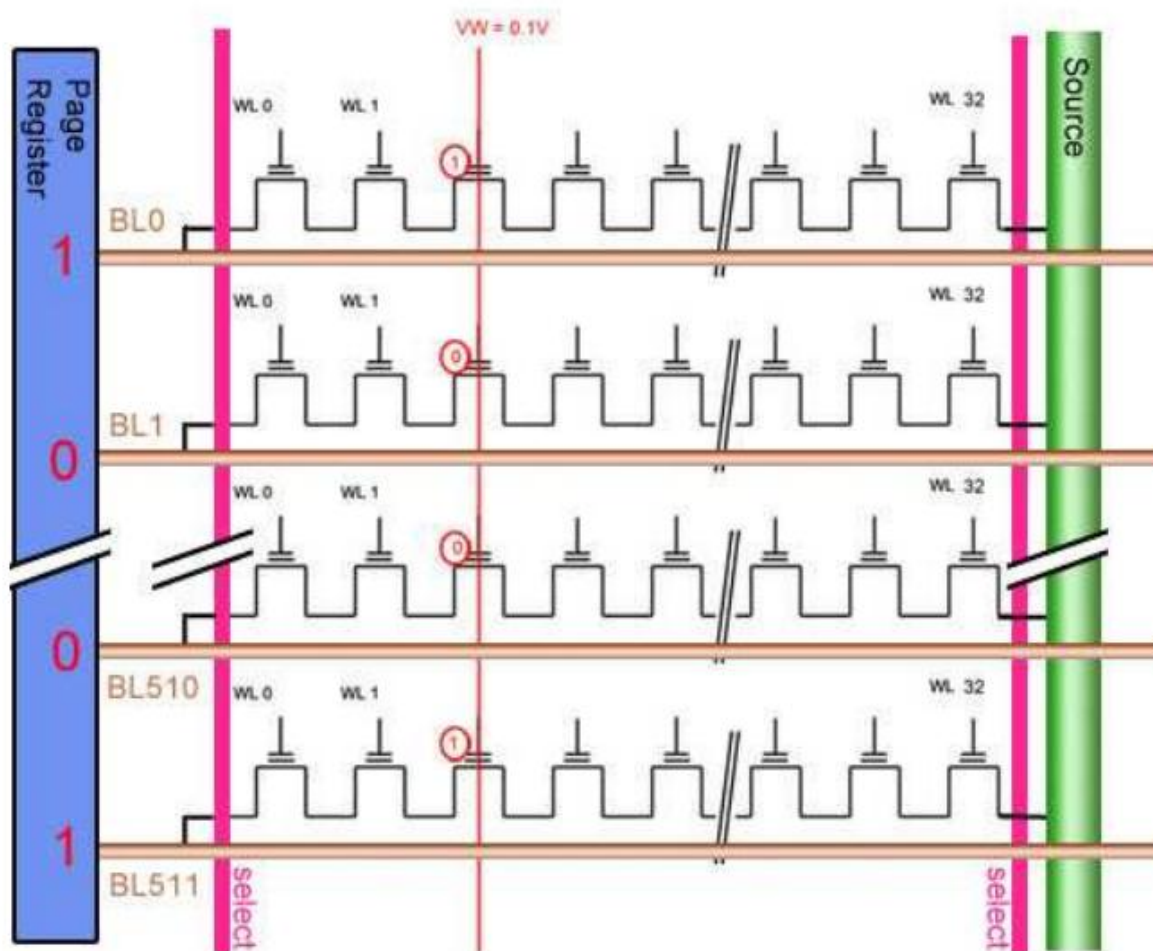


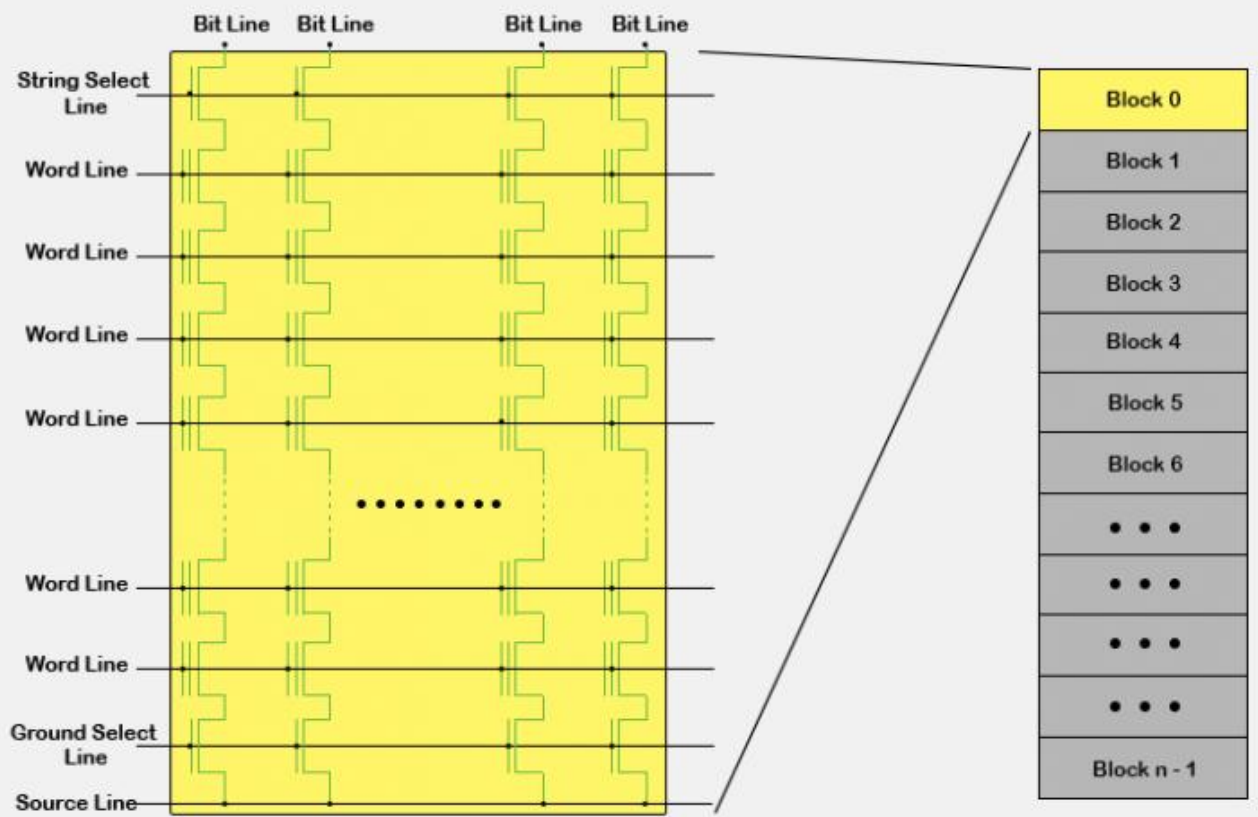


NAND String

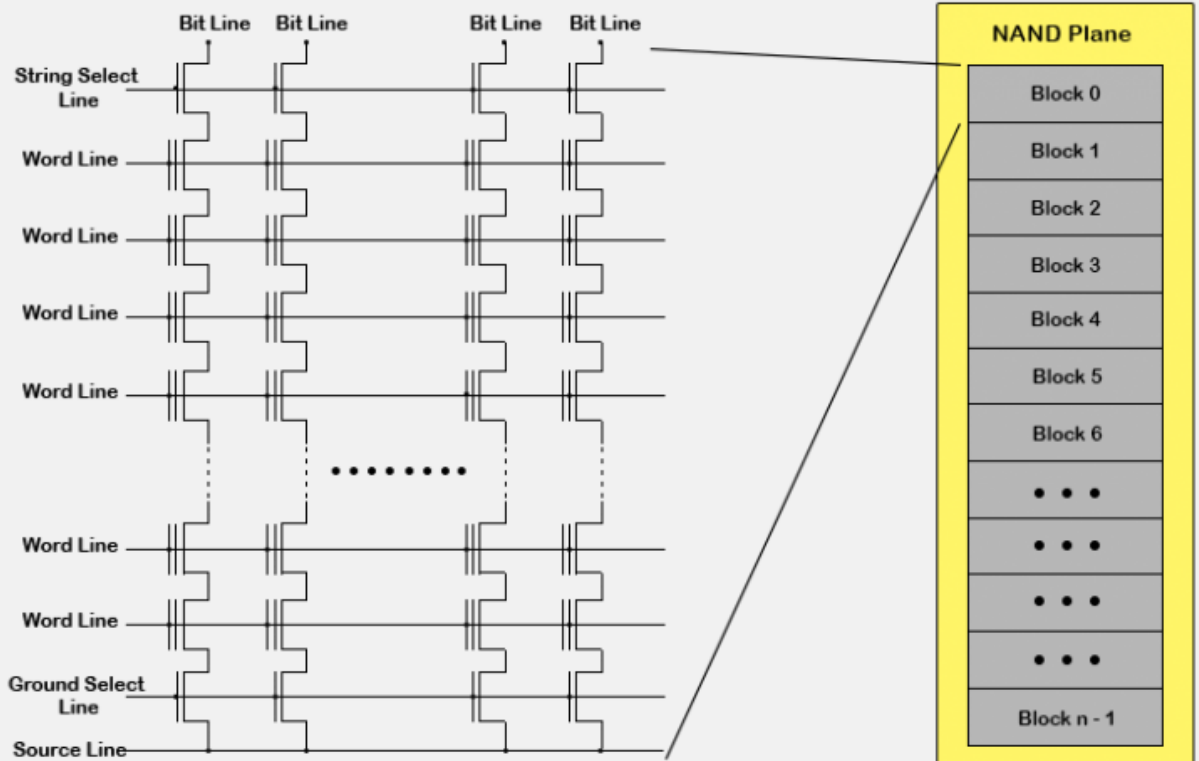




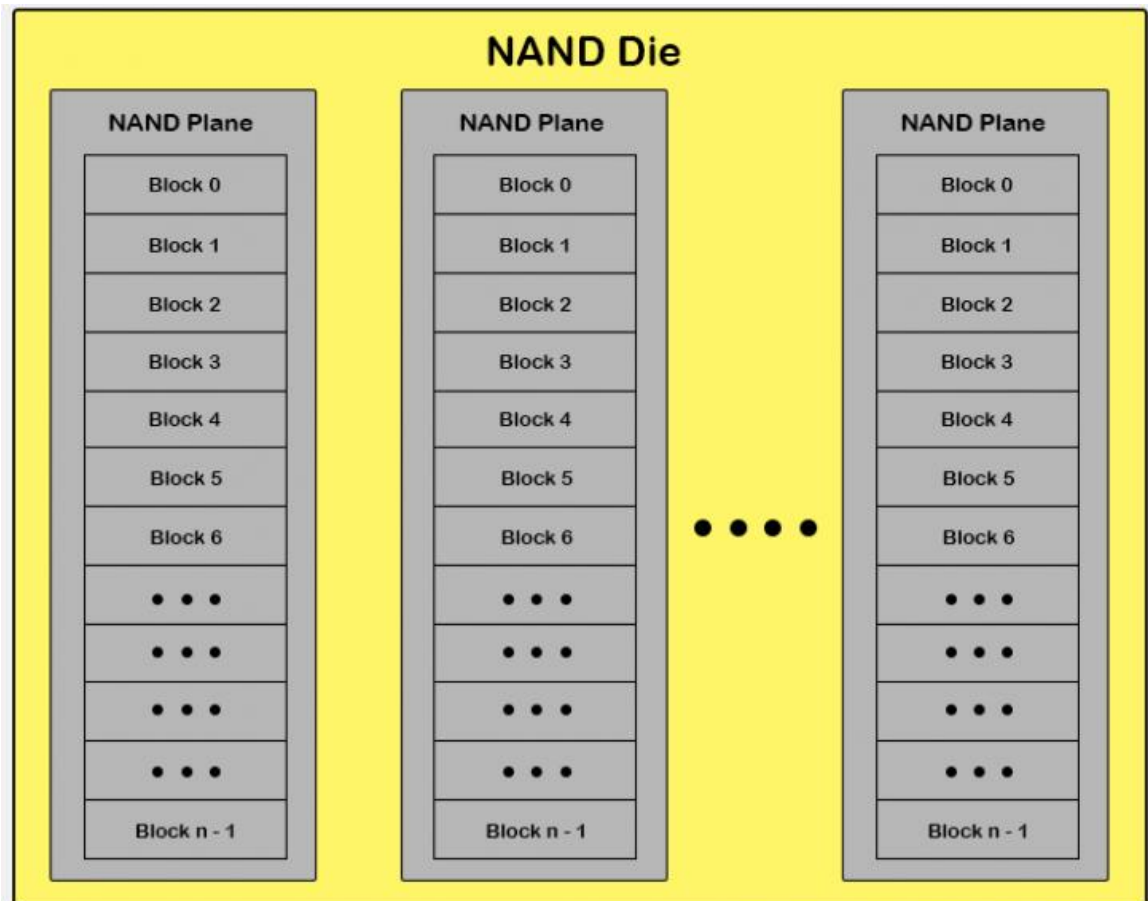




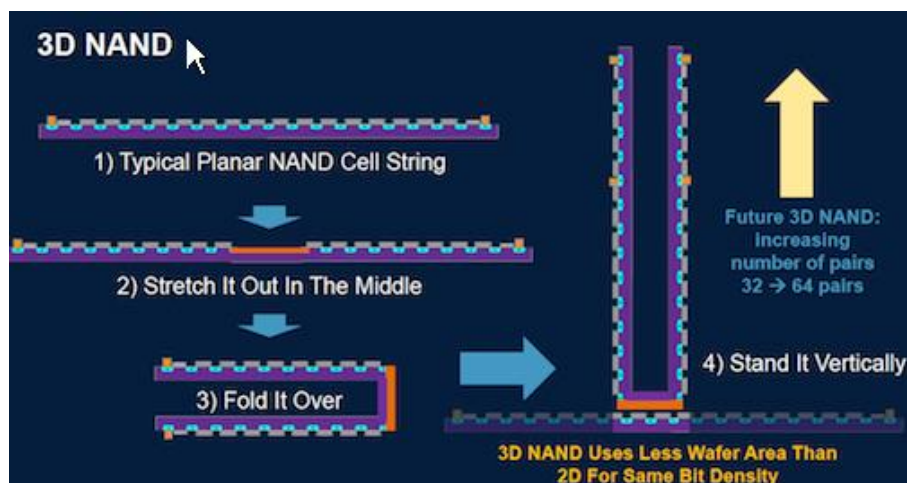
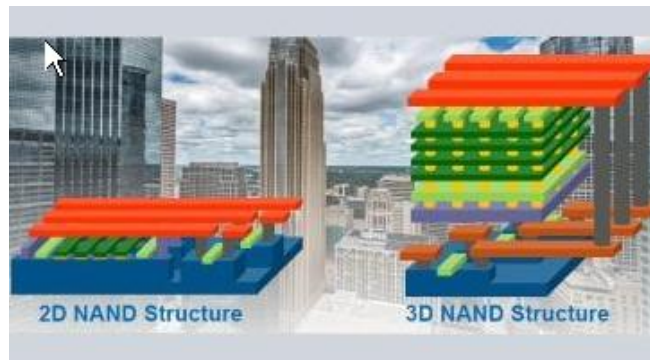
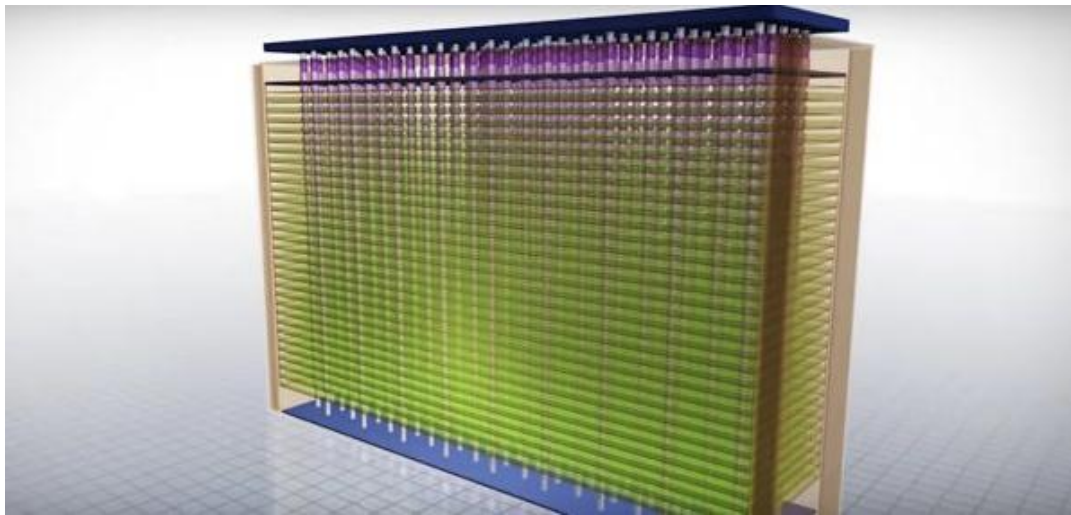
NAND Architecture - Block Structure

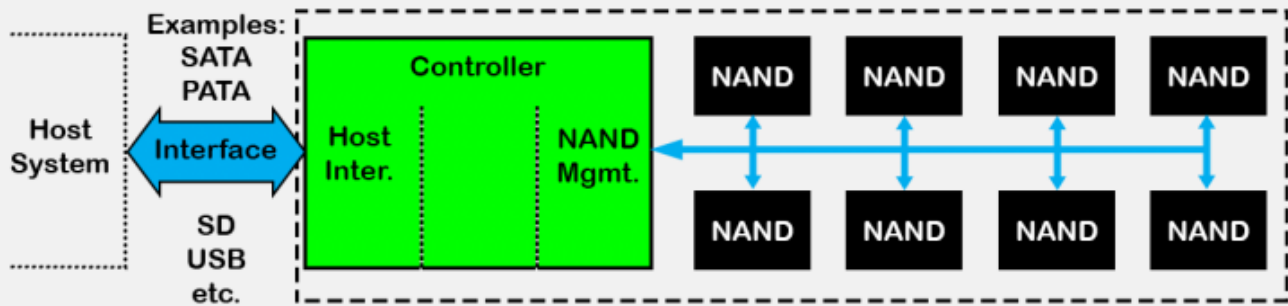


NAND Architecture - NAND Plane

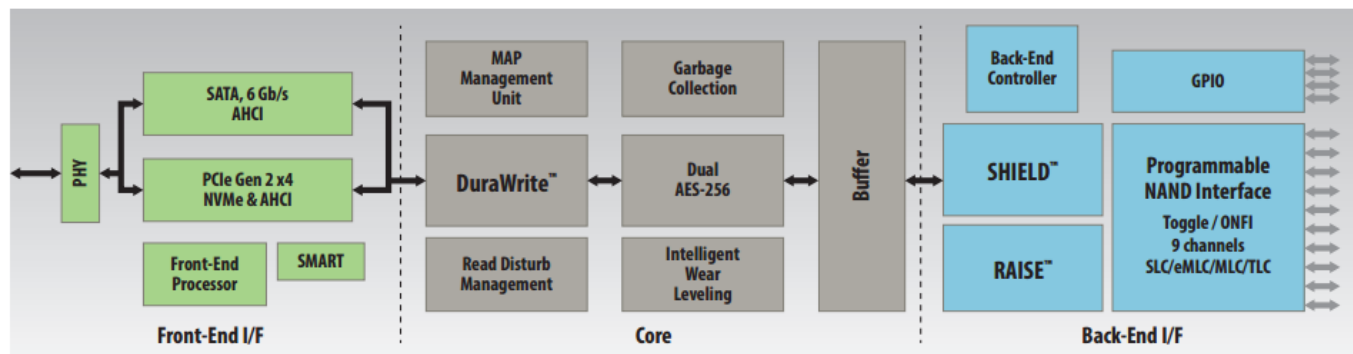


NAND Die with Multiple Planes





Basic Solid State Drive (SSD) Architecture



SF3700 Block Diagram

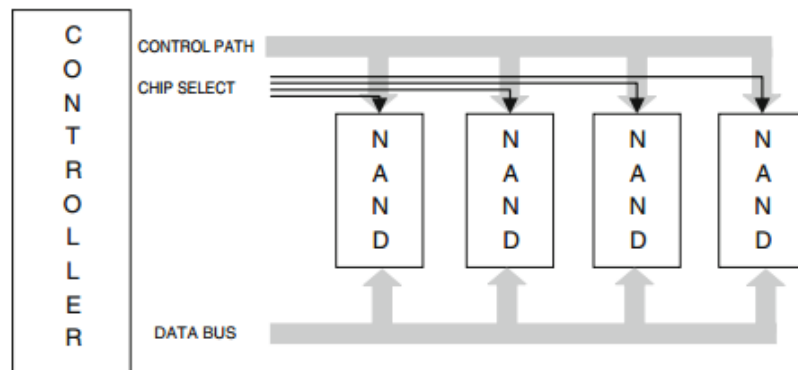


Fig. 5.12 Single-channel architecture

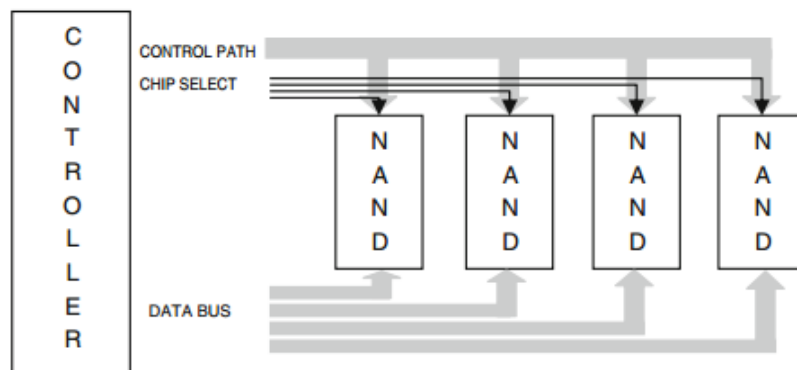


Fig. 5.13 Multichannel architecture

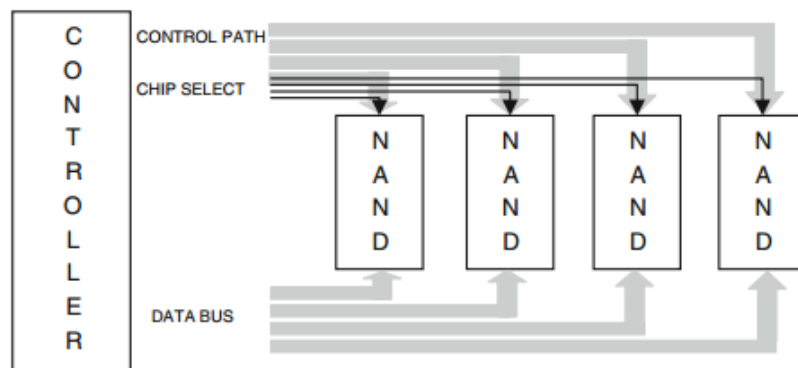
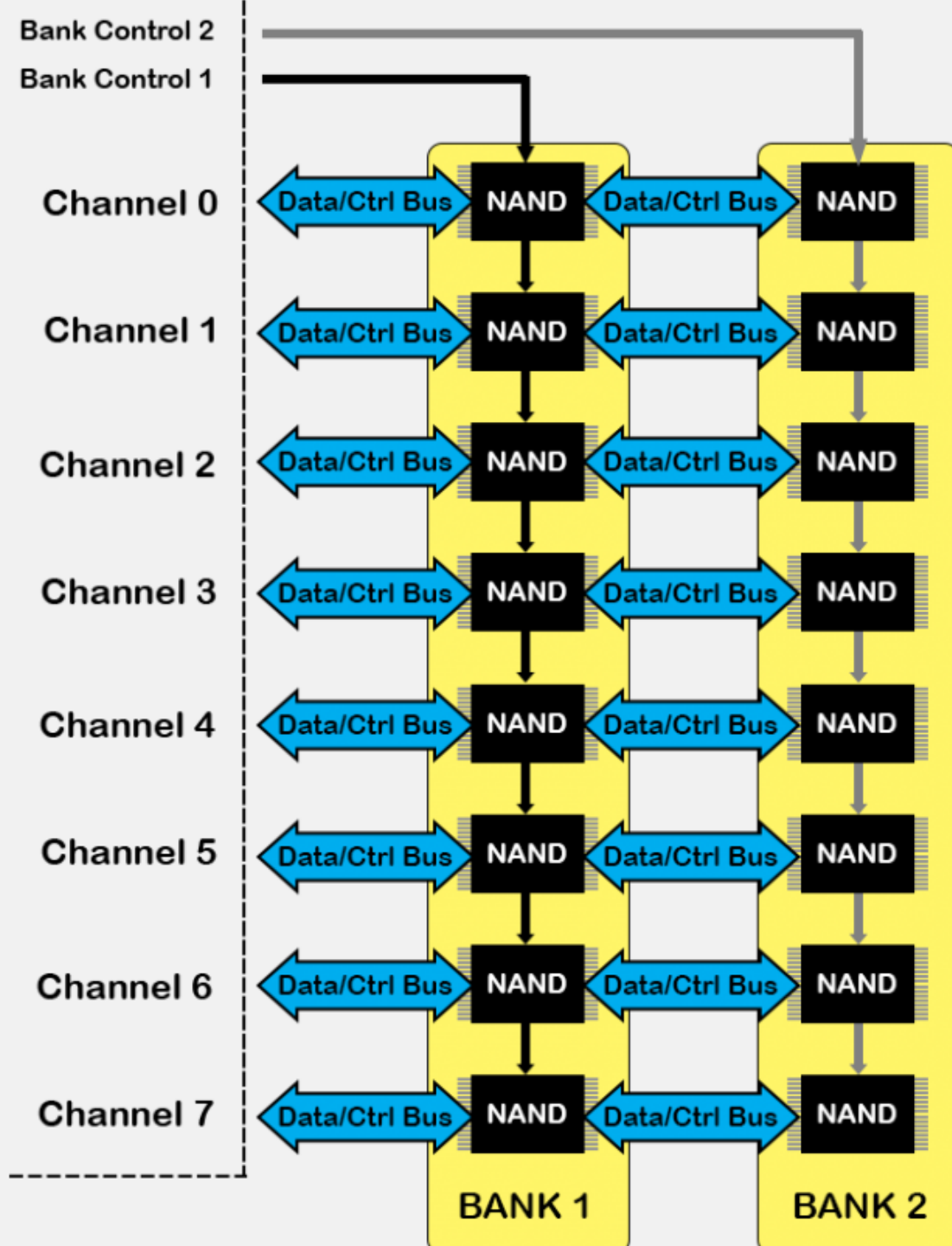
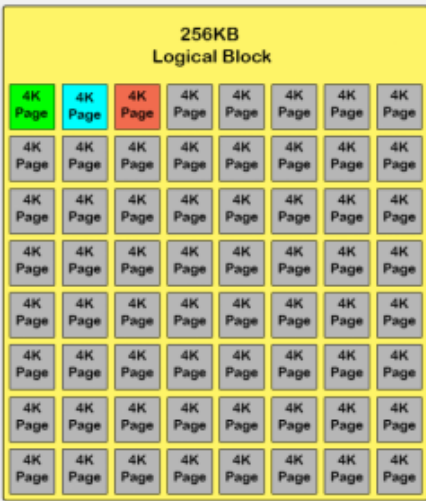


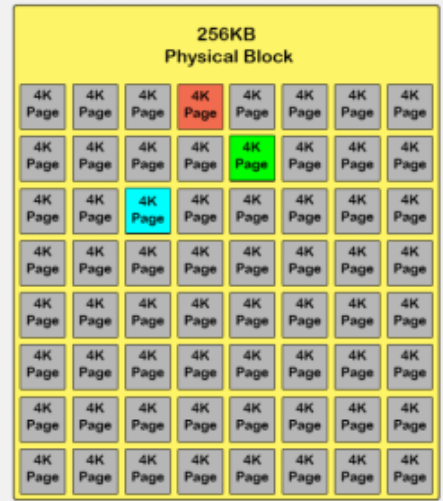
Fig. 5.14 Fully connected architecture



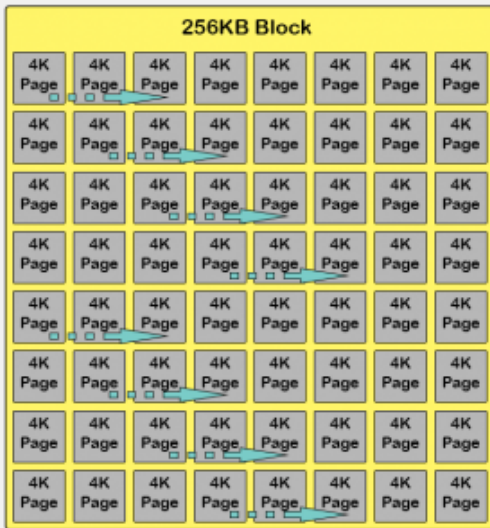
NAND Banks and Channels Illustration



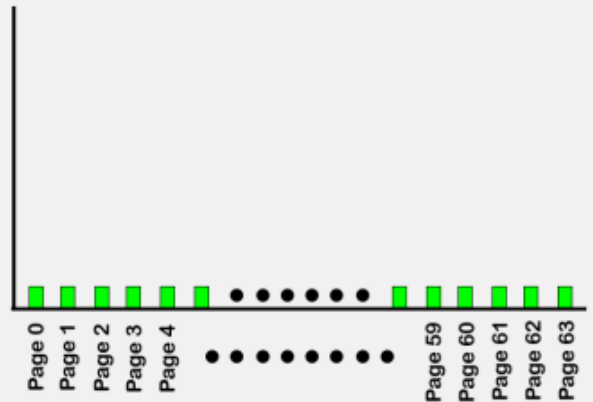
Translation Table	
Logical	Physical
Page 0	Page 12
Page 1	Page 18
Page 2	Page 3
⋮	⋮
Page x	Page y
Page x	Page y
Page x	Page y



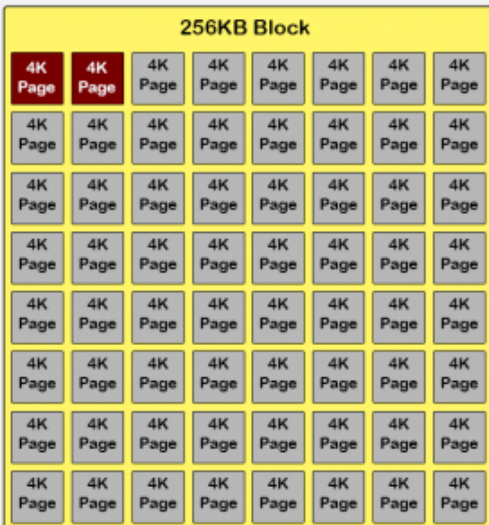
Logical to Physical Translation



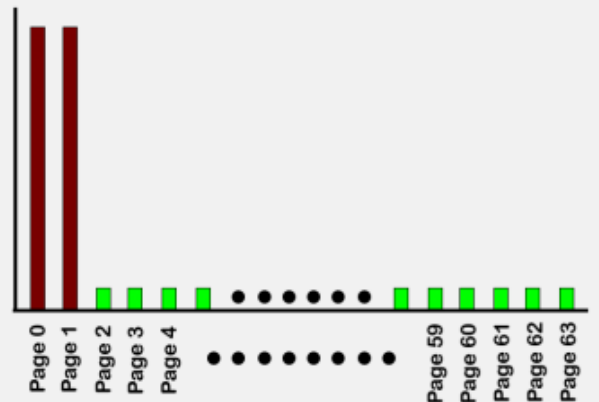
Number of Endurance Cycles per Page



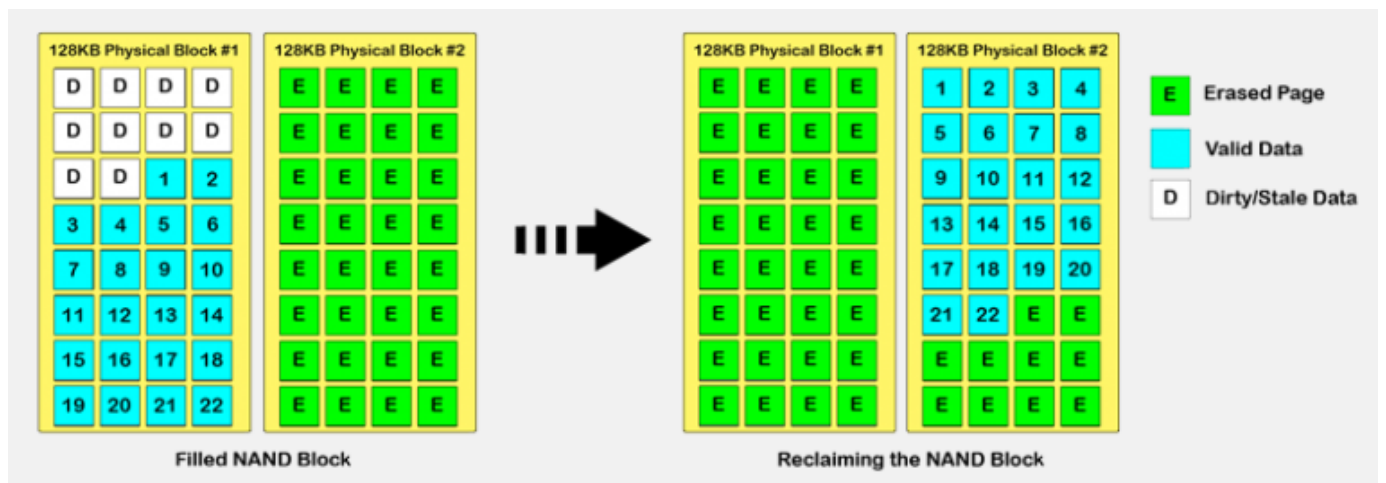
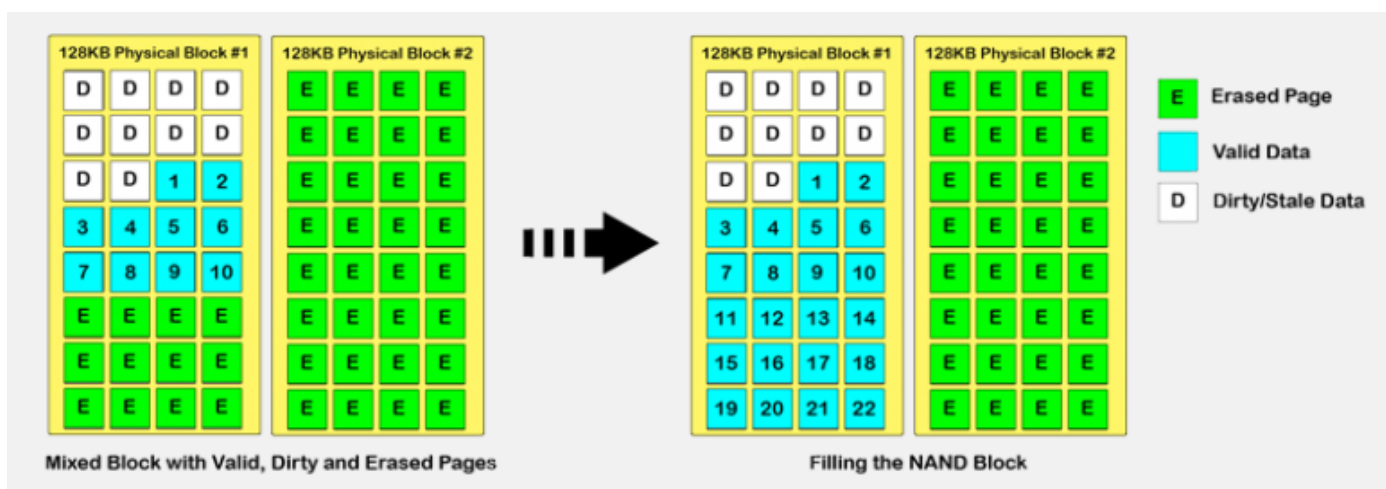
Sequentially Written Flash Block



Number of Endurance Cycles per Page



Non-Sequentially Written Flash Block

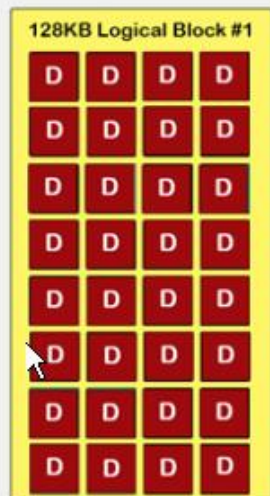


Write amplification

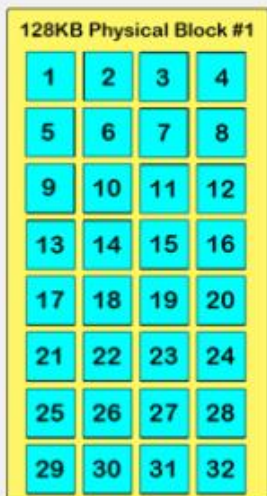
Write amplification (WA) is an SSD phenomenon that occurs when the actual amount of written physical data is more than the amount of logical data that is written by the host computer. There are two main factors that cause this difference: First, every storage device that uses NAND Flash memory is made of elements that must be erased before they can be rewritten. Second, while NAND Flash devices can be written a single page at a time (a page is typically 4KiB–16KiB), NAND Flash devices can only be erased one block at a time; and a block (also known as a "NAND block" or an "erase block") can contain hundreds of pages. This requires the internal movement of saved user data in background operations to free up adjacent pages of data that are eligible to be erased, and therefore available for new data written by the host computer. Consequently, the total number of actual writes to an SSD is typically more than the number of writes intended to be written by the host computer.



Deleted Data



What the Operating System Knows



What the SSD Controller Thinks



Erased Page



Valid Data

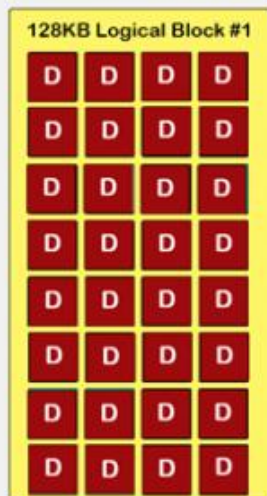


Dirty/Stale Data

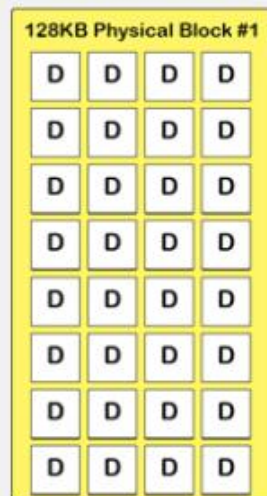
Without TRIM Command



Deleted Data



What the Operating System Knows



What the SSD Controller Thinks



Erased Page



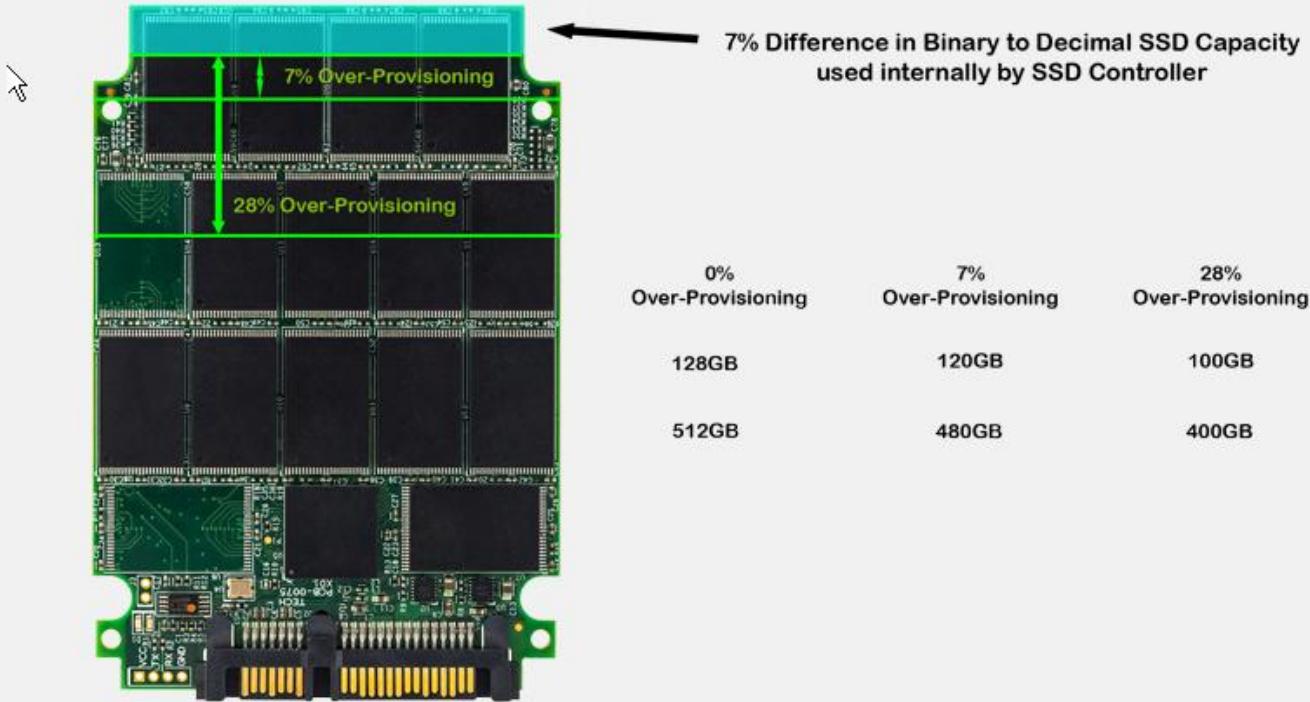
Valid Data



Dirty/Stale Data

With TRIM Command

Over-Provisioning at 0%, 7% and 28%



Marketed Capacity	IDEMA Decimal Capacity (Bytes)	Binary Capacity (Bytes)	Difference
128GB	128,035,676,160	137,438,953,472	7.34%
512GB	512,110,190,592	549,755,813,888	7.35%